

> Mechanical Specification:

(1) Dimension

- Chip size: $355 \pm 40 \mu\text{m} \times 280 \pm 40 \mu\text{m}$
- Thickness: 4.3 mil ($110 \pm 10 \mu\text{m}$)
- P bonding pad: 3.1 mil ($80 \pm 10 \mu\text{m}$)
- N bonding pad: 3.1 mil ($80 \pm 10 \mu\text{m}$)

(2) Metallization

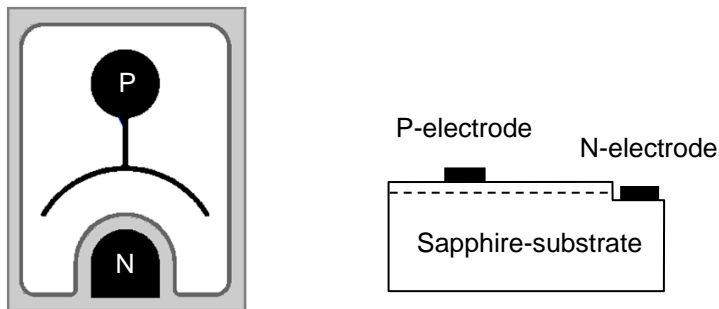
- Topside P electrode: Au alloy
- Topside N electrode: Au alloy

Features:

- High luminous intensity
- Long operation life
- 100% probing test
- Passivation layer on top

Applications:

- RGB display



Electro-optical Characteristics at 25°C: ⁽¹⁾

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit | |
|------------------------------------|--------|---------------------------|------|------|------|------|-----|
| Forward Voltage | Vf1 | If = 10μA | 2.0 | - | - | V | |
| | Vf2 | If = 20mA | - | 2.9 | 3.2 | V | |
| Reverse Current | Ir | Vr = 5V | - | - | 2.0 | μA | |
| Dominant Wavelength ⁽²⁾ | λd | If = 20mA | 460 | - | 475 | nm | |
| Spectra Half-width | Δλ | If = 20mA | - | 25 | - | nm | |
| Luminous intensity ⁽³⁾ | Iv | If = 20mA λd=460-465nm | I29 | 500 | - | 550 | mcd |
| | | | I30 | 550 | - | 600 | |
| | | | I31 | 600 | - | 650 | |
| | | If = 20mA λd=465-475nm | I30 | 550 | - | 600 | |
| | | | I31 | 600 | - | 650 | |
| | | | I32 | 650 | - | 700 | |
| | | | I33 | 700 | - | 750 | |
| | | | I34 | 750 | - | 800 | |
| | | | I35 | 800 | - | 850 | |
| | | | I36 | 850 | - | 900 | |

Note:

(1) ESD protection during chip handling is recommended.

(2) Basically, the wavelength span is 15nm; however, customers' special requirements are also welcome.

(3) Luminous intensity is measured by EPISTAR's equipment on bare chips.

> Absolute Maximum Ratings:

| Parameter | Symbol | Condition | Rating | Unit |
|------------------------------|--------|-----------------------------|-------------|------|
| Forward DC Current | If | Ta = 25°C | ≤ 35 | mA |
| Reverse Voltage | Vr | Ta = 25°C | ≤ 5 | V |
| Junction Temperature | Tj | - | ≤ 115 | °C |
| Storage Temperature | Tstg | Chip | -40 ~ +85 | °C |
| | | Chip-on-tape/storage | 5 ~ 35 | °C |
| | | Chip-on-tape/transportation | -20 ~ +65 | °C |
| Temperature during Packaging | - | - | 280(<10sec) | °C |

Note: Maximum ratings are package dependent. The above maximum ratings were determined using a Printed Circuit Board (PCB) without an encapsulant. Stresses in excess of the absolute maximum ratings such as forward current and junction temperature may cause damage to the LED.

> Characteristic Curves:

Fig.1 – Relative luminous Intensity vs. Forward Current

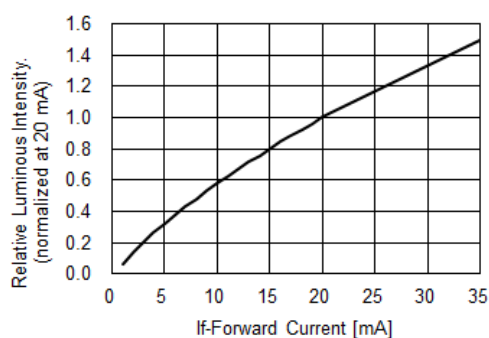


Fig.2 – Forward Current vs. Forward Voltage

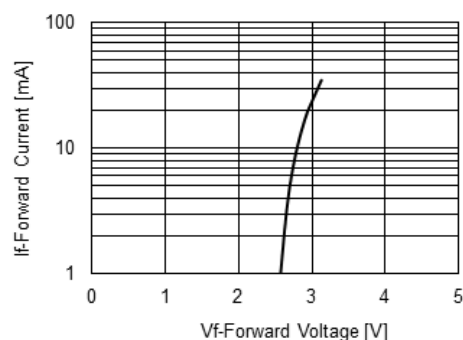


Fig.3 – Relative Intensity (@20mA) vs. Ambient Temperature

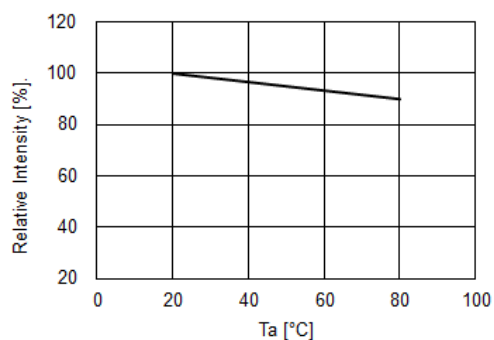


Fig.4 – Forward Voltage (@20mA) vs. Ambient Temperature

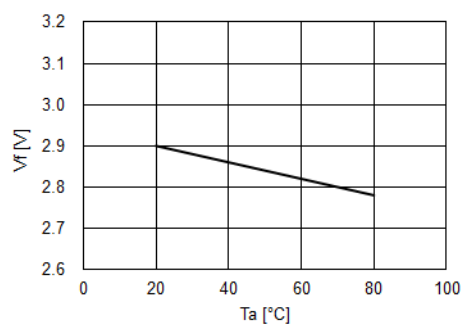


Fig.5 – Dominant Wavelength (@20mA) vs. Ambient Temperature

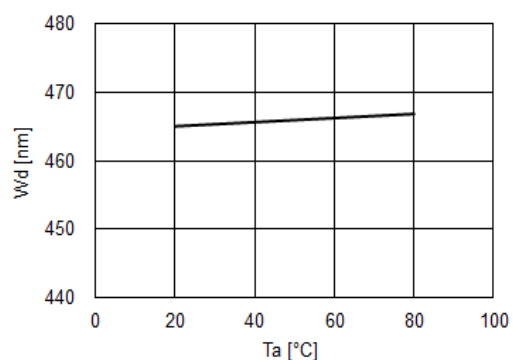


Fig.6 – Maximum Driving Forward DC Current vs. Ambient Temperature (De-rating based on Tj max. = 115°C)

